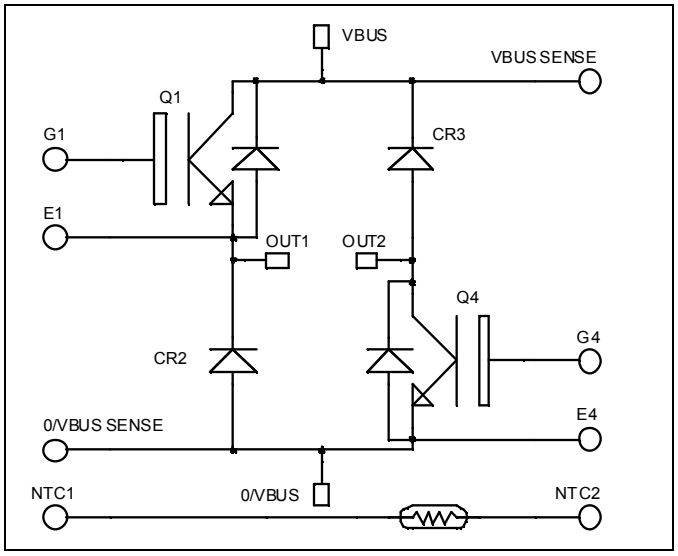
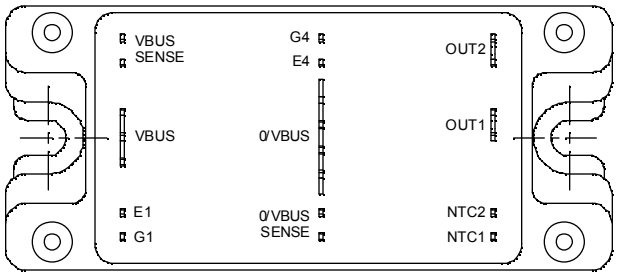
Asymmetrical - Bridge NPT IGBT Power Module

V_{CES} = 600V
I_C = 90A @ Tc = 80°C





Application

- Welding converters
- Switched Mode Power Supplies
- Switched Reluctance Motor Drives

Features

- Non Punch Through (NPT) Fast IGBT®
  - Low voltage drop
  - Low tail current
  - Switching frequency up to 100 kHz
  - Soft recovery parallel diodes
  - Low diode VF
  - Low leakage current
  - Avalanche energy rated
  - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- Very low stray inductance
  - Symmetrical design
  - Lead frames for power connections
- Internal thermistor for temperature monitoring
- High level of integration

Benefits

- Outstanding performance at high frequency operation
- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Easy paralleling due to positive TC of VCEsat
- Low profile
- RoHS compliant

Absolute maximum ratings

Symbol	*Parameter*		*Max ratings*	*Unit*
V_{CES}	Collector - Emitter Breakdown Voltage		600	V
I_C	Continuous Collector Current	T_c = 25°C	110	A
		T_c = 80°C	90	
I_{CM}	Pulsed Collector Current	T_c = 25°C	315	
V_{GE}	Gate – Emitter Voltage		±20	V
P_D	Maximum Power Dissipation	T_c = 25°C	416	W
RBSOA	Reverse Bias Safe Operating Area	T_j = 150°C	200A @ 600V	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handing Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

All ratings @ T_j = 25°C unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
I_{CES}	Zero Gate Voltage Collector Current	V_{GE} = 0V, V_{CE} = 600V	T_j = 25°C			250	µA
			T_j = 125°C			500	
$V_{CE(sat)}$	Collector Emitter saturation Voltage	V_{GE} =15V, I_C = 90A	T_j = 25°C		2.0	2.5	V
			T_j = 125°C		2.2		
$V_{GE(th)}$	Gate Threshold Voltage	V_{GE} = V_{CE}, I_C = 1mA		3		5	V
I_{GES}	Gate – Emitter Leakage Current	V_{GE} = 20 V, V_{CE} = 0V				±150	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
C_{ies}	Input Capacitance	V_{GE} = 0V, V_{CE} = 25V, f = 1MHz		4300		pF
C_{oes}	Output Capacitance			470		
C_{res}	Reverse Transfer Capacitance			400		
Q_g	Total gate Charge	V_{GE} = 15V, V_{Bus} = 300V, I_C = 90A		330		nC
Q_{ge}	Gate – Emitter Charge			290		
Q_{gc}	Gate – Collector Charge			200		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (25°C), V_{GE} = 15V, V_{Bus} = 400V, I_C = 90A, R_G = 5 Ω		26		ns
T_r	Rise Time			25		
$T_{d(off)}$	Turn-off Delay Time			150		
T_f	Fall Time			30		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (125°C), V_{GE} = 15V, V_{Bus} = 400V, I_C = 90A, R_G = 5 Ω		26		ns
T_r	Rise Time			25		
$T_{d(off)}$	Turn-off Delay Time			170		
T_f	Fall Time			40		
E_{on}	Turn-on Switching Energy	V_{GE} = 15V, V_{Bus} = 400V, I_C = 90A, R_G = 5 Ω, T_j = 125°C		4.3		mJ
E_{off}	Turn-off Switching Energy	V_{GE} = 15V, V_{Bus} = 400V, I_C = 90A, R_G = 5 Ω, T_j = 125°C		3.5		

Diode ratings and characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
V_{RRM}	Maximum Peak Repetitive Reverse Voltage			600			V
I_{RM}	Maximum Reverse Leakage Current	V_R=600V	T_j = 25°C			250	µA
			T_j = 125°C			500	
I_F	DC Forward Current		T_c = 80°C		100		A
V_F	Diode Forward Voltage	I_F = 100 A			1.6	1.8	V
		I_F = 200 A			1.9		
		I_F = 100 A	T_j = 125°C		1.4		
t_{rr}	Reverse Recovery Time	I_F = 100A, V_R = 400V, di/dt =200A/µs	T_j = 25°C		180		ns
			T_j = 125°C		220		
Q_{rr}	Reverse Recovery Charge		T_j = 25°C		390		nC
			T_j = 125°C		1450		

Thermal and package characteristics

Symbol	Characteristic			Min	Typ	Max	Unit
R_{thJC}	Junction to Case Thermal Resistance		IGBT			0.3	°C/W
			Diode			0.55	
V_{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, I isol<1mA, 50/60Hz			2500			V
T_J	Operating junction temperature range			-40		150	°C
T_{STG}	Storage Temperature Range			-40		125	
T_C	Operating Case Temperature			-40		100	
Torque	Mounting torque	To Heatsink	M5	2.5		4.7	N.m
Wt	Package Weight					160	g

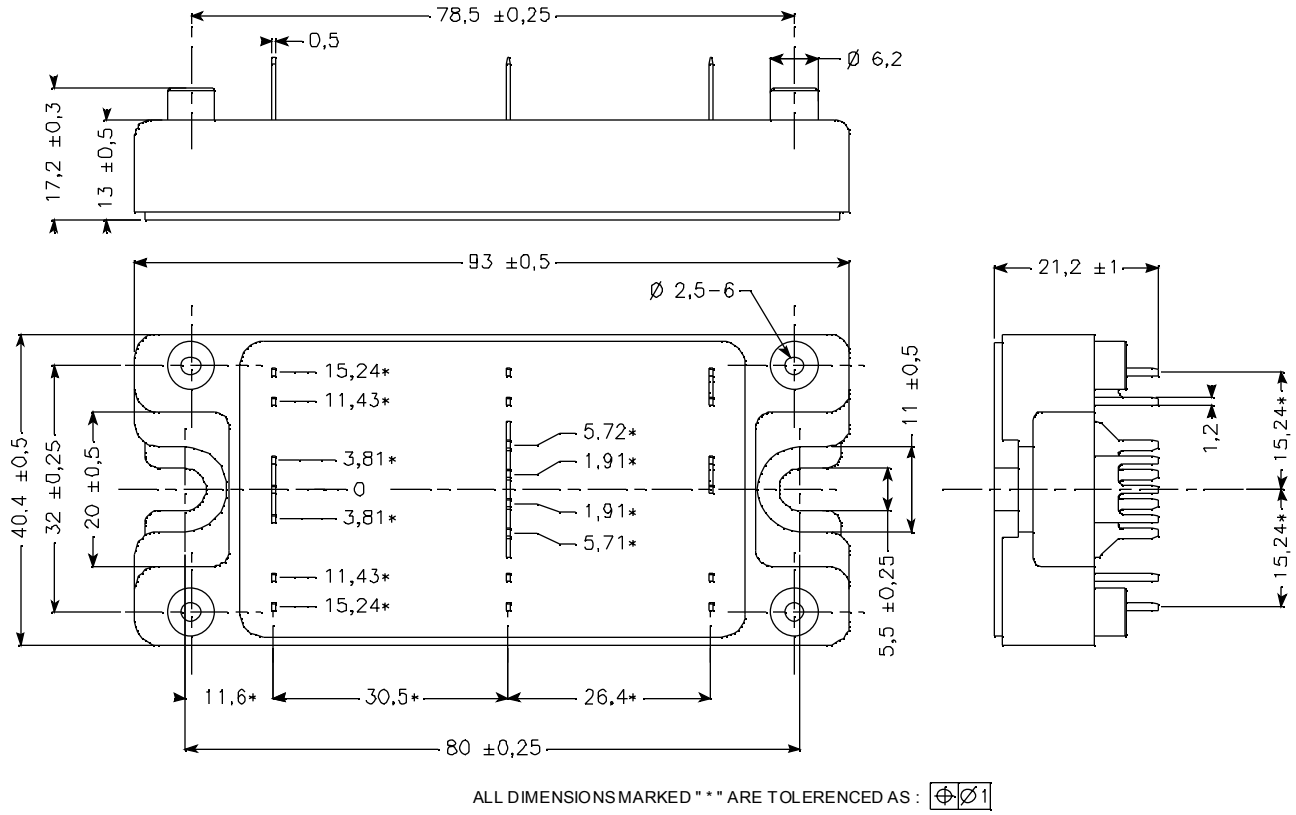
Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

Symbol	Characteristic	Min	Typ	Max	Unit
R_{25}	Resistance @ 25°C		50		kΩ
$B_{25/85}$	T_{25} = 298.15 K		3952		K

$$R_T = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]}$$

T: Thermistor temperature
R_T: Thermistor value at T

SP4 Package outline (dimensions in mm)

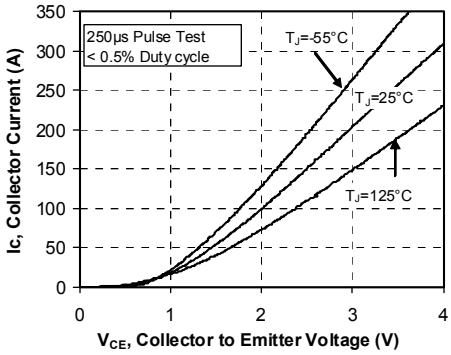


ALL DIMENSIONS MARKED " * " ARE TOLERENCED AS : ⊕ Ø 1

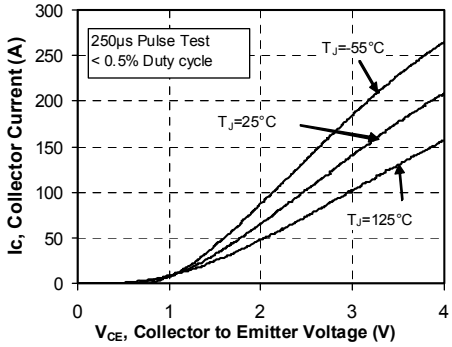
See application note APT0501 - Mounting Instructions for SP4 Power Modules on www.microsemi.com

Typical Performance Curve

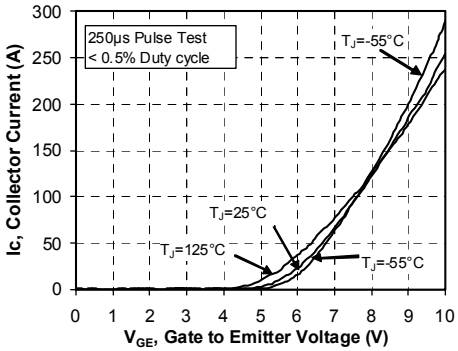
Output characteristics (V_{GE}=15V)



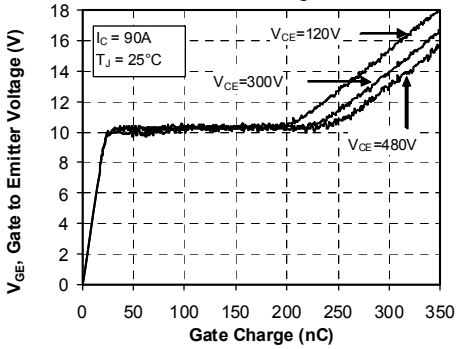
Output Characteristics (V_{GE}=10V)



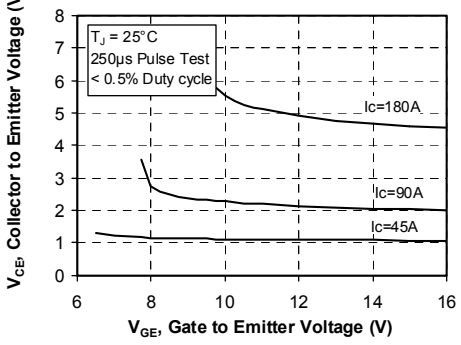
Transfer Characteristics



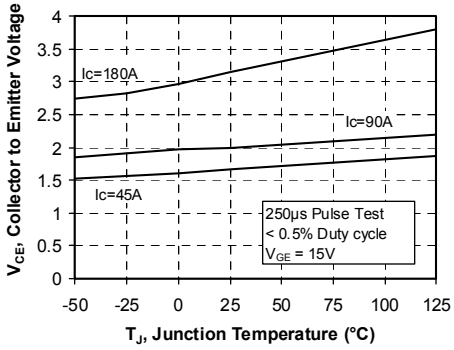
Gate Charge



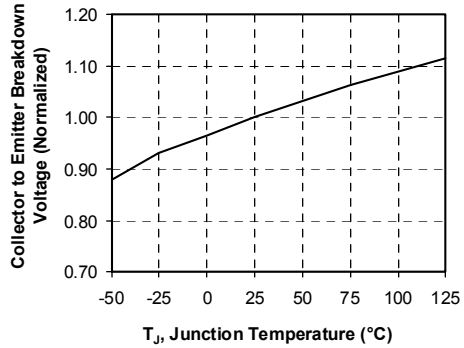
On state Voltage vs Gate to Emitter Volt.



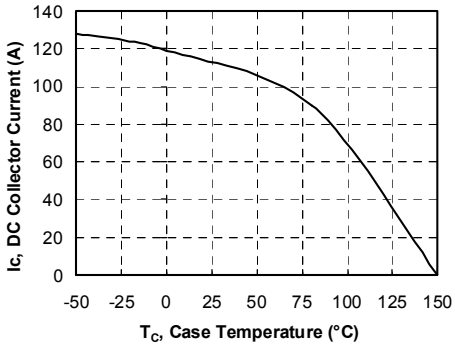
On state Voltage vs Junction Temperature



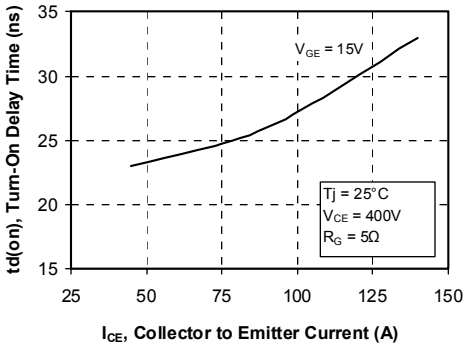
Breakdown Voltage vs Junction Temp.



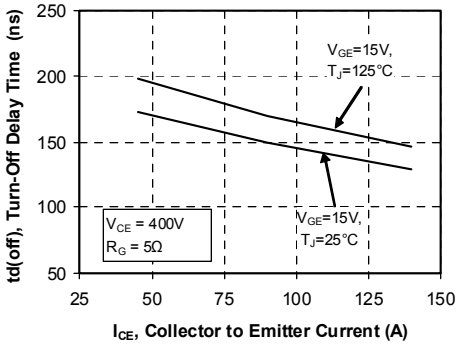
DC Collector Current vs Case Temperature



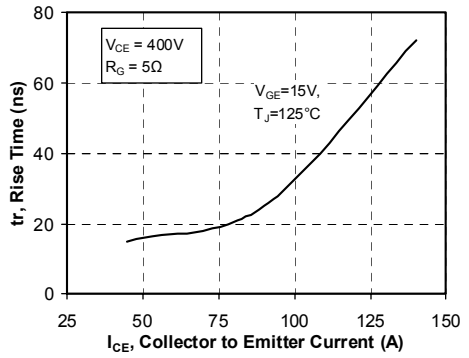
Turn-On Delay Time vs Collector Current



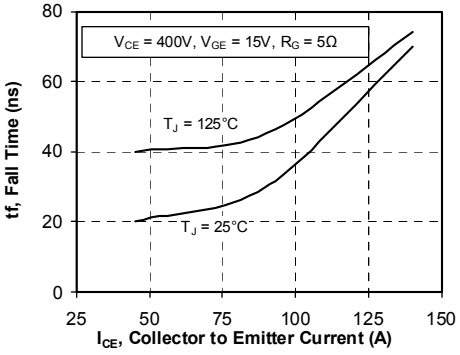
Turn-Off Delay Time vs Collector Current



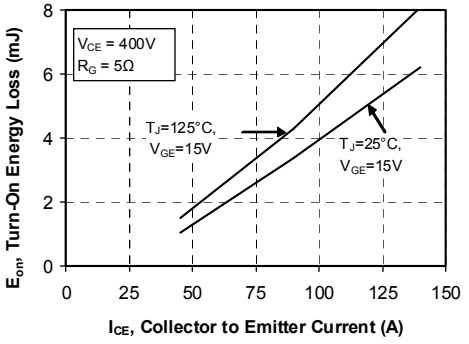
Current Rise Time vs Collector Current



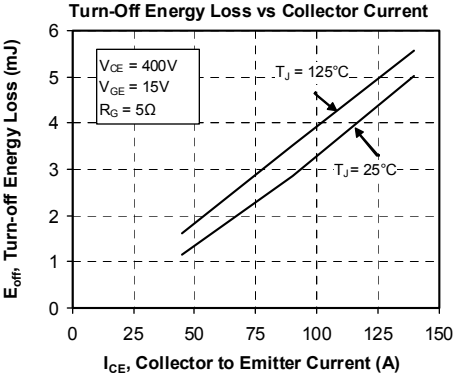
Current Fall Time vs Collector Current



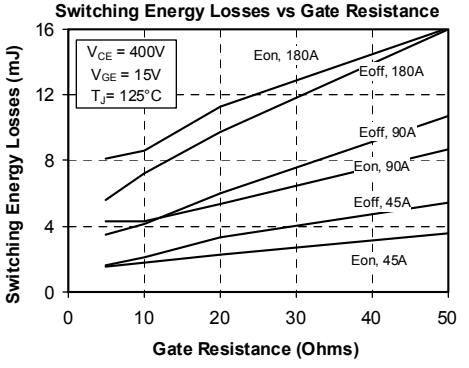
Turn-On Energy Loss vs Collector Current



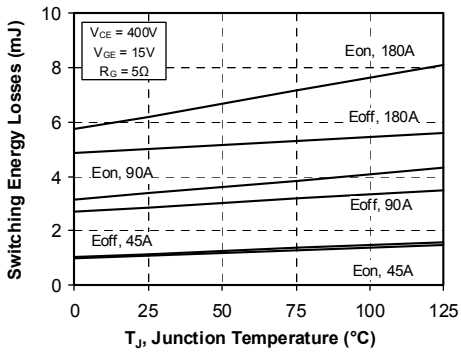
Turn-Off Energy Loss vs Collector Current



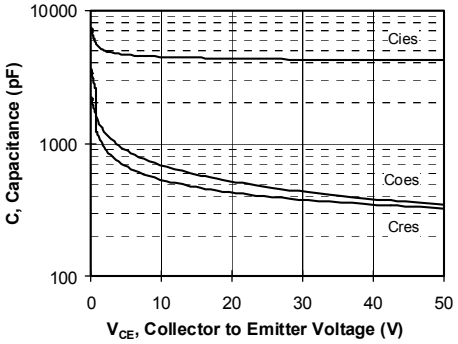
Switching Energy Losses vs Gate Resistance



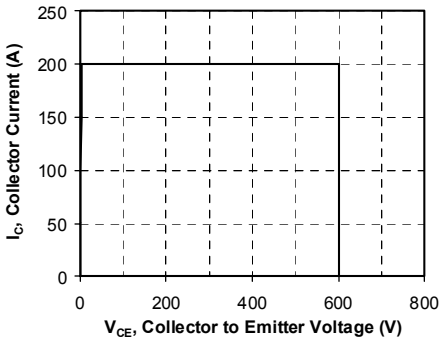
Switching Energy Losses vs Junction Temp.



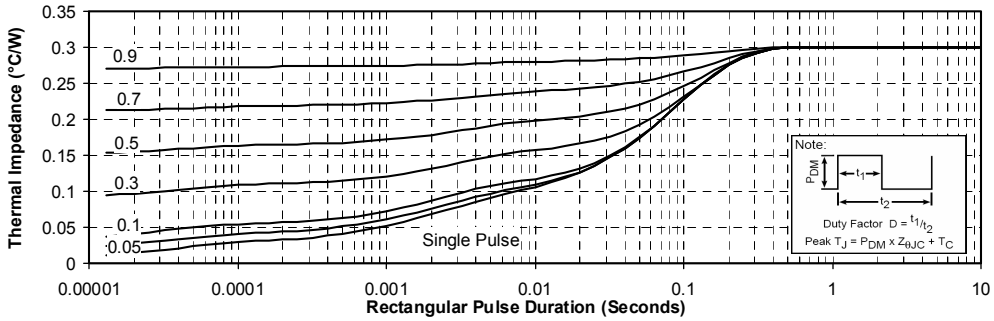
Capacitance vs Collector to Emitter Voltage



Reverse Bias Safe Operating Area



Maximum Effective Transient Thermal Impedance, Junction to Case vs Pulse Duration



Operating Frequency vs Collector Current